



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	Package	I _D T _A = +25°C
-20V	$52m\Omega @V_{GS} = -4.5V$	SOT23	-5.0A
-200	100mΩ @V _{GS} = -2.5V	30123	-3.6A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

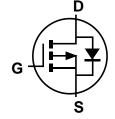
Features

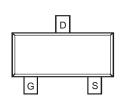
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMG230UXQ</u>)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)







Top View

Internal Schematic

Top View

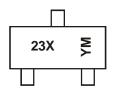
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMG2305UX-7	Standard	SOT23	3,000/Tape & Reel
DMG2305UX-13	Standard	SOT23	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



23X = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	W	~	D	Е	F	G	Н	ı	J	K	L	M	N
Mon	th	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Coc	le	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Drain Current (Note 5) \/ 45\/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		-4.2 -3.3	А
Continuous Drain Current (Note 5) V _{GS} = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-5.0 -4.0	А
Pulsed Drain Current (Note 6)		I _{DM}	-10	А	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		P_{D}	1.4	W
Thermal Desistance Junction to Ambient (Note 5)	Steady State	D	90	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	64	°C/W
Thermal Resistance, Junction to Case (Note 7)		R ₀ JC	33	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

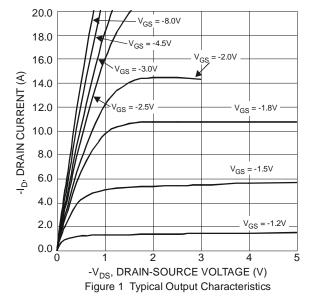
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

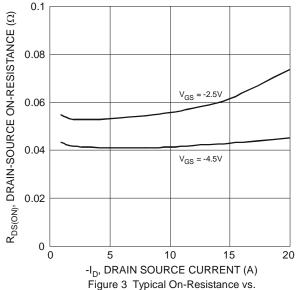
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			40	52		$V_{GS} = -4.5V$, $I_D = -4.2A$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	52	100	$m\Omega$	$V_{GS} = -2.5V, I_D = -3.4A$		
			68	200		$V_{GS} = -1.8V, I_D = -2A$		
Forward Transfer Admittance	Y _{FS}	_	9		S	$V_{DS} = -5V, I_{D} = -4A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{ISS}	_	808	_	pF	V 45V V 0V		
Output Capacitance	Coss	_	85		рF	$V_{DS} = -15V, V_{GS} = 0V$ - f = 1.0MHz		
Reverse Transfer Capacitance	C _{RSS}	_	77		рF	1 – 1.001112		
Gate Resistance	R _G		15.2		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
SWITCHING CHARACTERISTICS (Note 8)								
Total Gate Charge	Q_G	_	10.2	_	nC	\\ 4 E\\ \\ 4\\		
Gate-Source Charge	Q_GS	_	1.3	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $I_{D} = -3.5A$		
Gate-Drain Charge	Q_{GD}	_	2.2	_	nC	ID = -3.3A		
Turn-On Delay Time	t _{D(ON)}	_	10.8	_	ns			
Turn-On Rise Time	t _R	_	13.7	_	ns	$V_{DS} = -4V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	79.3	_	ns	$R_G = 6\Omega$, $I_D = -1A$		
Turn-Off Fall Time	t _F	_	34.7	_	ns	1		

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing







Drain Current and Gate Voltage

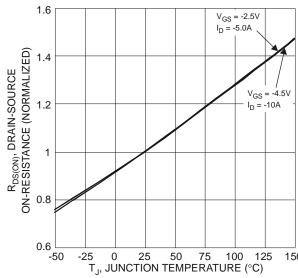
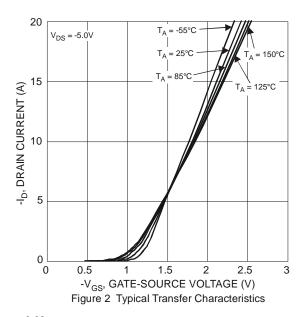
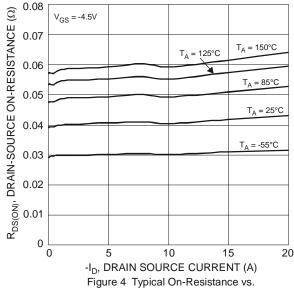
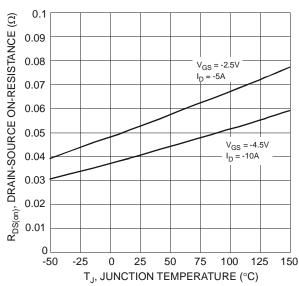


Figure 5 On-Resistance Variation with Temperature





Drain Current and Temperature





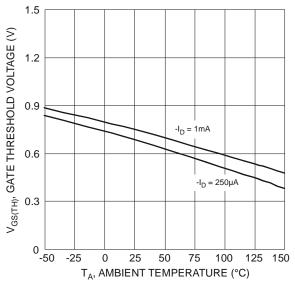
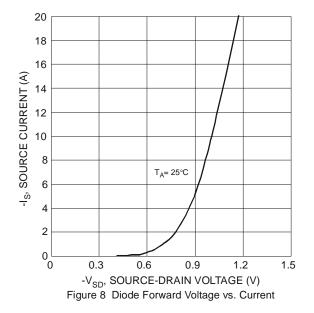


Figure 7 Gate Threshold Variation vs. Ambient Temperature

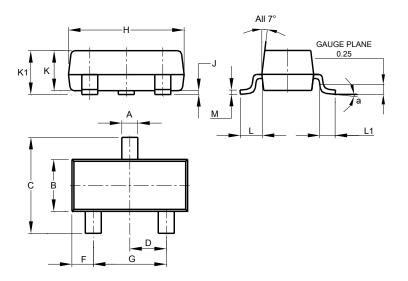




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

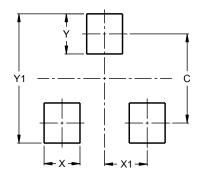


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
H	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°	_				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
V1	2.0			



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